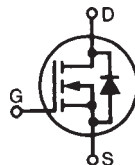


Polar™ Power MOSFET

HiPerFET™

IXFV22N50P
IXFV22N50PS
IXFH22N50P

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

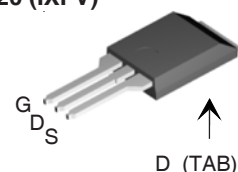


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^{\circ}\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^{\circ}\text{C}$ to 150°C , $R_{GS} = 1\text{M}\Omega$	500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^{\circ}\text{C}$	22	A
I_{DM}	$T_C = 25^{\circ}\text{C}$, Pulse Width Limited by T_{JM}	50	A
I_A	$T_C = 25^{\circ}\text{C}$	22	A
E_{AS}	$T_C = 25^{\circ}\text{C}$	750	mJ
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^{\circ}\text{C}$	10	V/ns
P_D	$T_C = 25^{\circ}\text{C}$	350	W
T_J		-55 ... +150	$^{\circ}\text{C}$
T_{JM}		150	$^{\circ}\text{C}$
T_{stg}		-55 ... +150	$^{\circ}\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^{\circ}\text{C}$
T_{SOLD}	Plastic Body for 10s	260	$^{\circ}\text{C}$
M_d	Mounting Torque (TO-247)	1.13/10	Nm/lb.in.
F_C	Mounting Force (PLUS 220)	11..65/2.5..14.6	N/lb.
Weight	TO-247	6	g
	PLUS 220 types	4	g

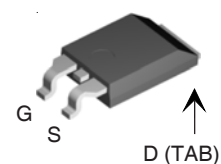
Symbol	Test Conditions ($T_J = 25^{\circ}\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 2.5\text{mA}$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0\text{V}$ $T_J = 125^{\circ}\text{C}$			15 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1			270 m Ω

$$\begin{aligned} V_{DSS} &= 500\text{V} \\ I_{D25} &= 22\text{A} \\ R_{DS(on)} &\leq 270\text{m}\Omega \\ t_{rr} &\leq 200\text{ns} \end{aligned}$$

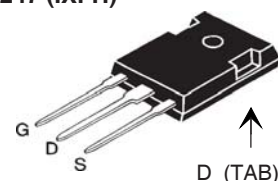
PLUS220 (IXFV)



PLUS220SMD (IXFV_S)



TO-247 (IXFH)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International Standard Packages
- Avalanche Rated
- Fast Intrinsic Diode
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switched-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

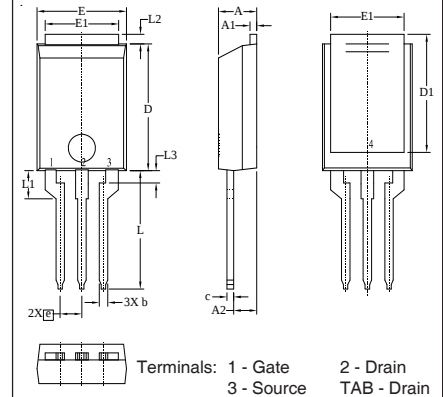
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}, I_D = 0.5 \cdot I_{D25}$, Note 1	12	20	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		2880	pF
C_{oss}			310	pF
C_{rss}			29	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)		22	ns
t_r			25	ns
$t_{d(off)}$			72	ns
t_f			21	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		50	nC
Q_{gs}			16	nC
Q_{gd}			18	nC
R_{thJC}	(TO-247 & PLUS220)			0.35 $^\circ\text{C/W}$
R_{thCS}		0.25		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			22 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			88 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 22\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			200 ns
Q_{RM}			0.7	μC
I_{RM}			7.0	A

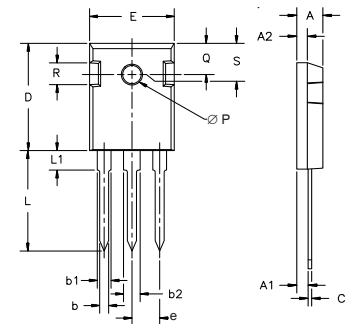
Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

PLUS220 (IXFV) Outline



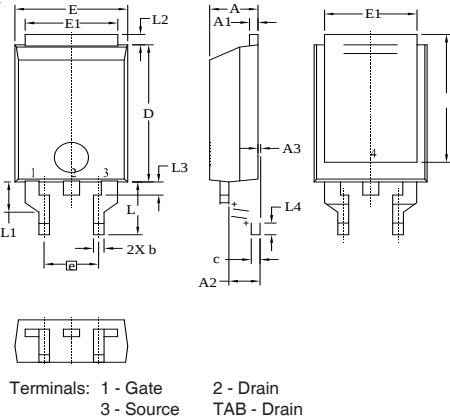
SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.028	.035	0.70	0.90
A2	.098	.118	2.50	3.00
b	.035	.047	0.90	1.20
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D1	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E1	.331	.346	8.40	8.80
e	.100	BSC	2.54	BSC
L	.512	.551	13.00	14.00
L1	.118	.138	3.00	3.50
L2	.035	.051	0.90	1.30
L3	.047	.059	1.20	1.50

TO-247 (IXFH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

PLUS220SMD (IXFV_S) Outline

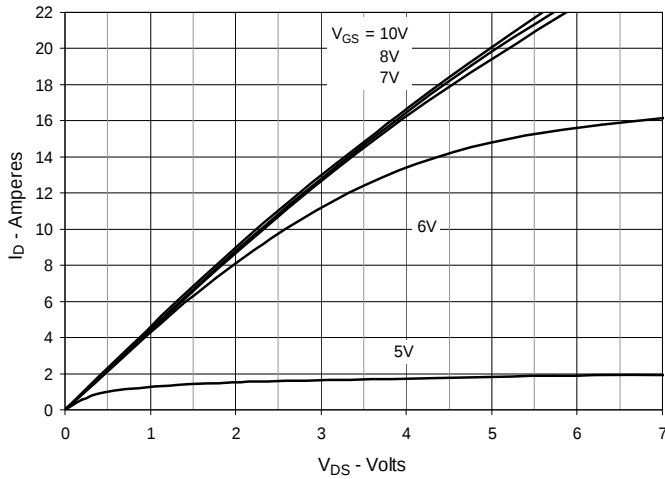


SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.028	.035	0.70	0.90
A2	.098	.118	2.50	3.00
A3	.000	.010	0.00	0.25
b	.035	.047	0.90	1.20
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D1	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E1	.331	.346	8.40	8.80
e	.200	BSC	5.08	BSC
L	.209	.228	5.30	5.80
L1	.118	.138	3.00	3.50
L2	.035	.051	0.90	1.30
L3	.047	.059	1.20	1.50
L4	.039	.059	1.00	1.50

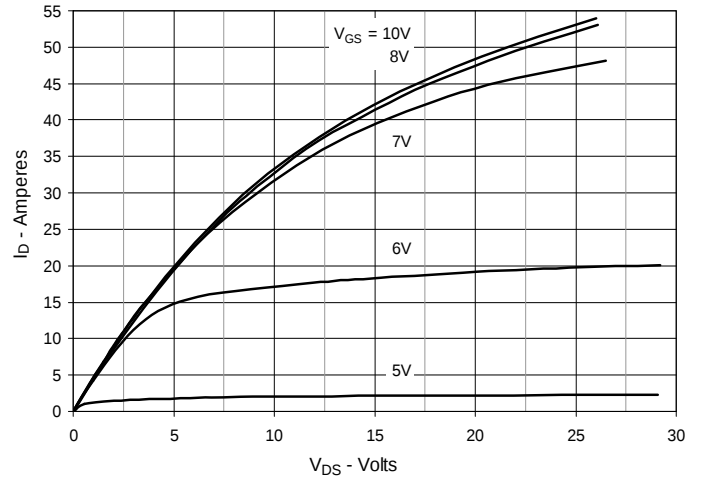
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338 B2
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

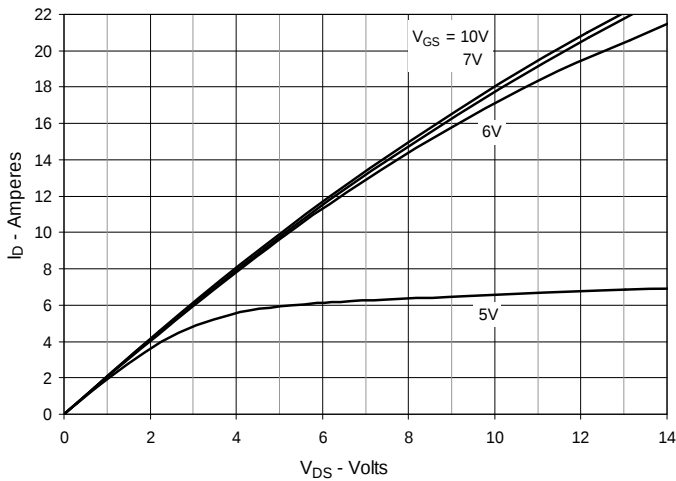
**Fig. 1. Output Characteristics
@ 25°C**



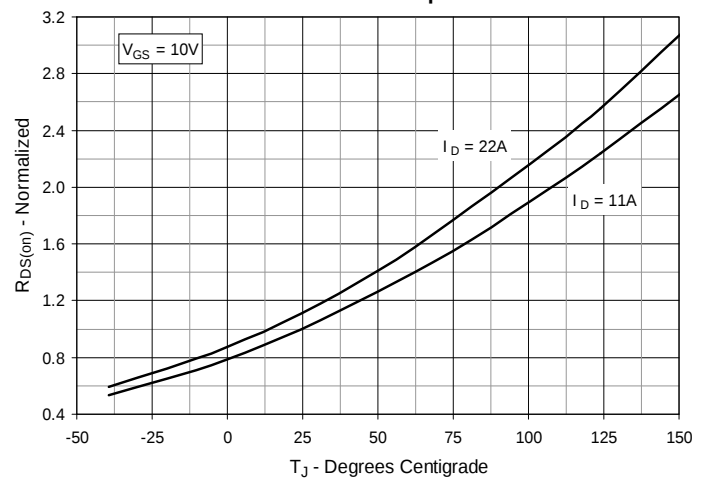
**Fig. 2. Extended Output Characteristics
@ 25°C**



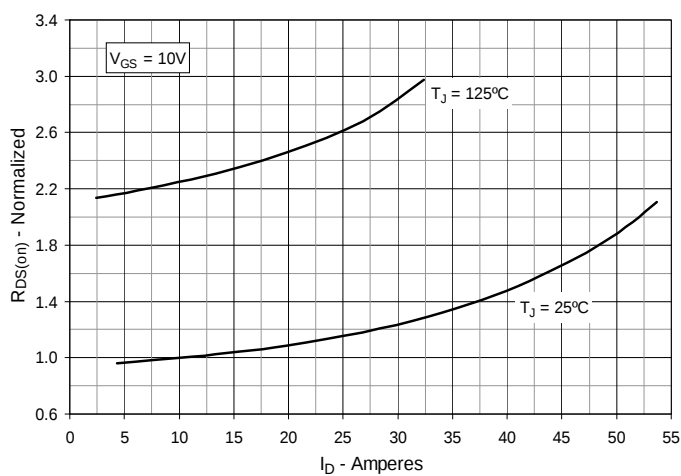
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 11A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 11A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

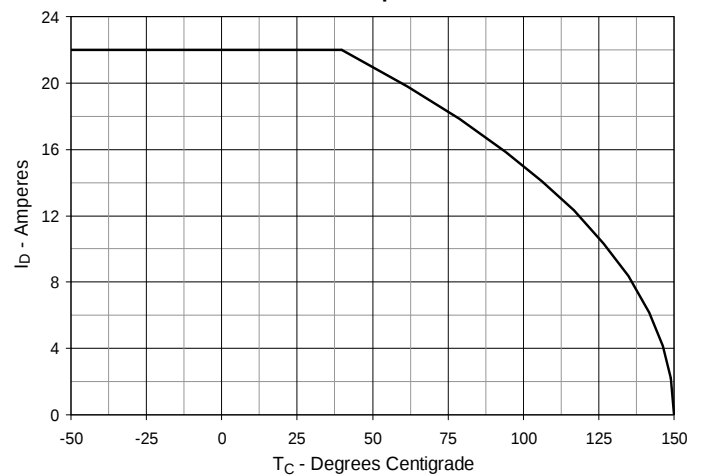


Fig. 7. Input Admittance

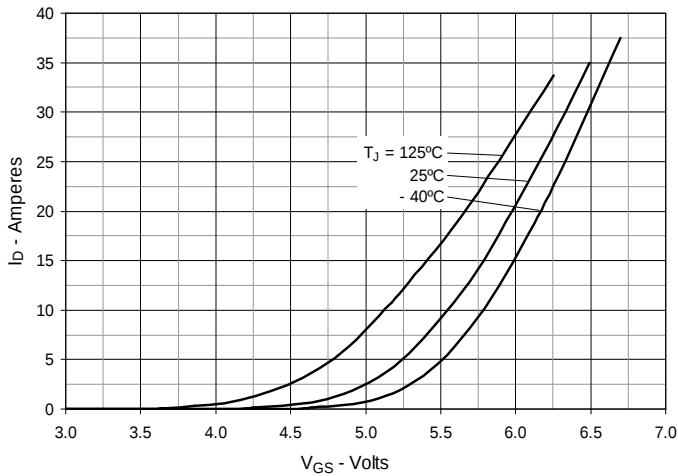


Fig. 8. Transconductance

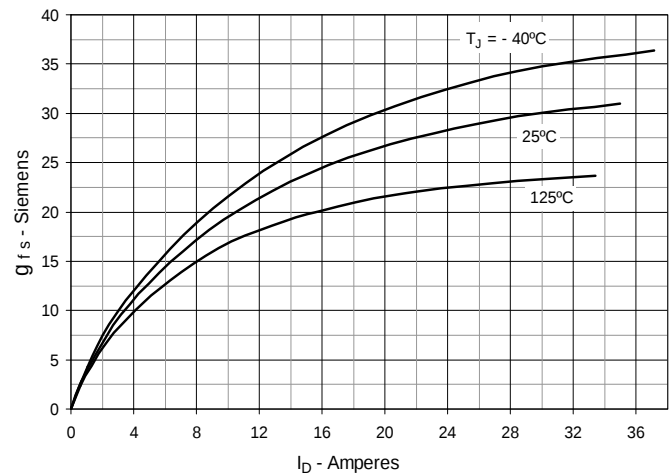


Fig. 9. Forward Voltage Drop of Intrinsic Diode

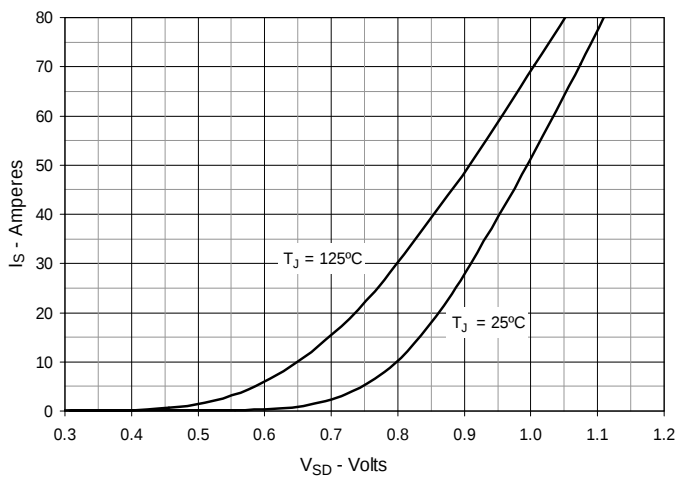


Fig. 10. Gate Charge

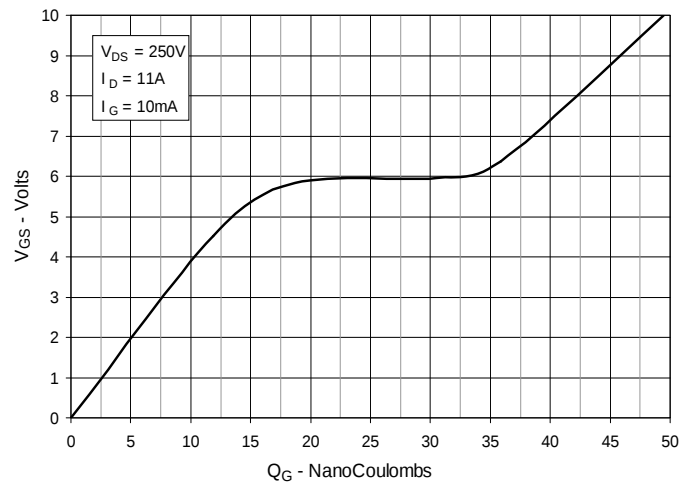


Fig. 11. Capacitance

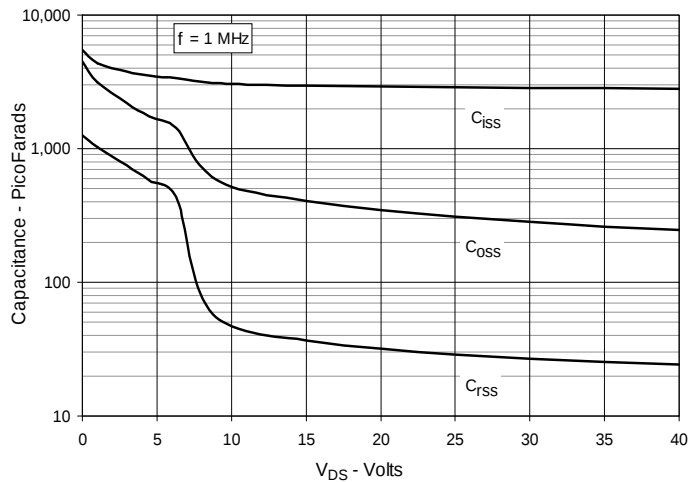


Fig. 12. Forward-Bias Safe Operating Area

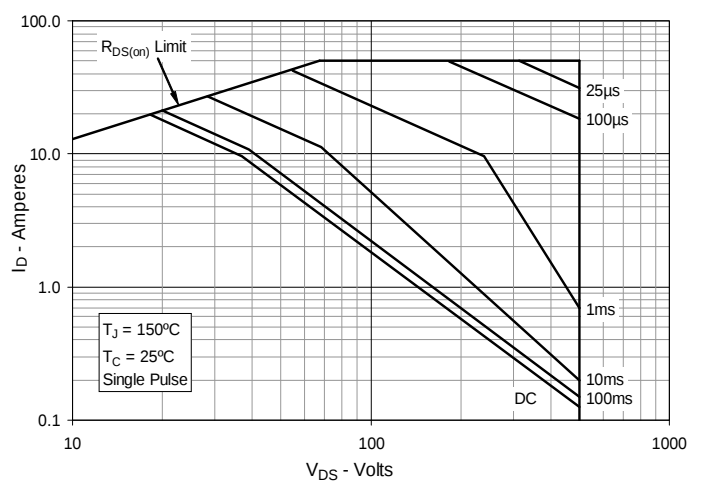


Fig. 13. Maximum Transient Thermal Impedance

